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Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Extended temperature range T_i = 175 °C
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Tin-plated 100 % solderable side pads for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- Trench MOSFET technology

3. Applications

- · Relay driver
- High-speed line driver
- Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-------------------|----------------------------------|---|-----|-----|-----|-----|------|
| V_{DS} | drain-source voltage | T _j = 25 °C | | - | - | 30 | V |
| V_{GS} | gate-source voltage | | | -20 | - | 20 | V |
| I _D | drain current | V_{GS} = 10 V; T_{amb} = 25 °C; $t \le 5$ s | [1] | - | - | 5.1 | Α |
| Static characte | Static characteristics | | | | | | |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 3.9 \text{ A}; T_j = 25 \text{ °C}$ | | - | 54 | 72 | mΩ |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6cm².



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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|-----------------------|----------------|
| 1 | D | drain | 15/ | D |
| 2 | D | drain | 7 | |
| 3 | G | gate | 2 5 | G ← |
| 4 | S | source | 3 8 94 | |
| 5 | D | drain | Transparent top view | |
| 6 | D | drain | DFN2020MD-6 (SOT1220) | 8 |
| 7 | D | drain | | 017aaa255 |
| 8 | S | source | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | age | | | | | |
|-------------|-------------|---|---------|--|--|--|--|
| | Name | Description | Version | | | | |
| PMPB100ENE | DFN2020MD-6 | DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals | SOT1220 | | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMPB100ENE | 3Т |

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|-------------------------|---|-----|-----|-----|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | 30 | V |
| V_{GS} | gate-source voltage | | | -20 | 20 | V |
| I _D | drain current | V _{GS} = 10 V; T _{amb} = 25 °C; t ≤ 5 s | [1] | - | 5.1 | Α |
| | | V _{GS} = 10 V; T _{amb} = 25 °C | [1] | - | 3.9 | А |
| | | V _{GS} = 10 V; T _{amb} = 100 °C | [1] | - | 2.4 | Α |
| I _{DM} | peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$ | | - | 16 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [1] | - | 2 | W |
| | | T _{amb} = 25 °C; t ≤ 5 s | [1] | - | 3.3 | W |
| | | T _{sp} = 25 °C | | - | 10 | W |
| T _j | junction temperature | | | -55 | 175 | °C |
| T _{amb} | ambient temperature | | | -55 | 175 | °C |
| T _{stg} | storage temperature | | | -65 | 175 | °C |
| Source Drain D | iode | | • | | | |
| I _S | source current | T _{amb} = 25 °C | [1] | - | 1.9 | А |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6cm².

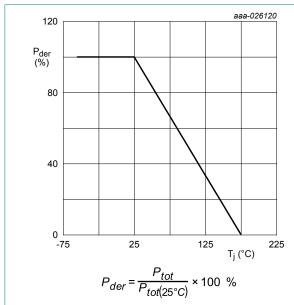


Fig. 1. Normalized total power dissipation as a function of junction temperature

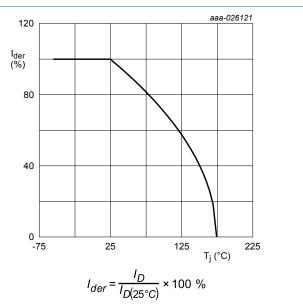


Fig. 2. Normalized continuous drain current as a function of junction temperature

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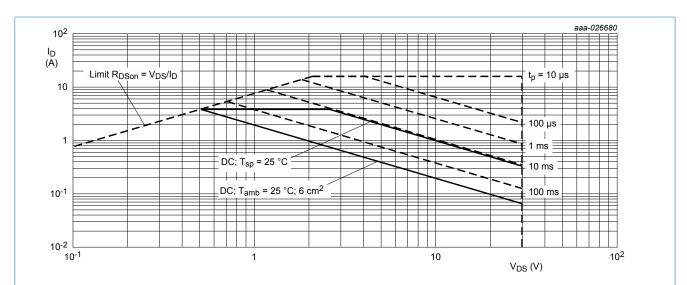


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

30 V, N-channel MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--|----------------------|-----|-----|-----|-----|------|
| R _{th(j-a)} | thermal resistance from junction to ambient | | [1] | - | 236 | 272 | K/W |
| | | | [2] | - | 67 | 77 | K/W |
| | | in free air; t ≤ 5 s | [2] | - | 36 | 45 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | 12 | 15 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

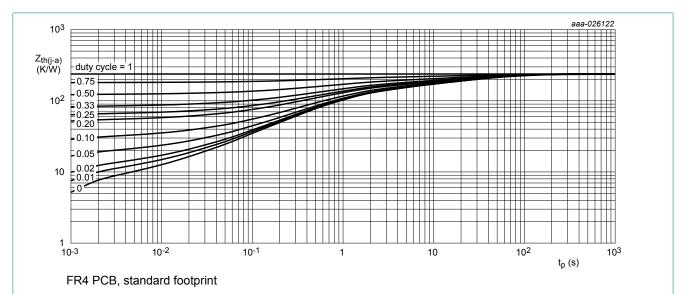


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

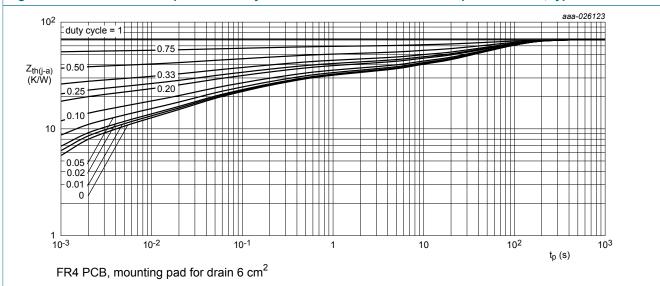


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|-----------------------------------|---|-----|------|----------|------|
| Static chara | acteristics | | | | <u> </u> | ' |
| V _{(BR)DSS} | drain-source breakdown voltage | I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C | 30 | - | - | V |
| V_{GSth} | gate-source threshold voltage | I_D = 250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C | 1 | 1.5 | 2.5 | V |
| I _{DSS} | drain leakage current | V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C | - | - | 1 | μΑ |
| I _{GSS} | gate leakage current | V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 10 | μΑ |
| | | V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -10 | μΑ |
| | | V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 2 | μΑ |
| | | V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -2 | μΑ |
| R _{DSon} | drain-source on-state | V _{GS} = 10 V; I _D = 3.9 A; T _j = 25 °C | - | 54 | 72 | mΩ |
| resistance | resistance | V _{GS} = 10 V; I _D = 3.9 A; T _j = 175 °C | - | 98 | 130 | mΩ |
| | | V_{GS} = 4.5 V; I_D = 3.3 A; T_j = 25 °C | - | 70 | 100 | mΩ |
| g _{fs} | forward transconductance | V_{DS} = 10 V; I_{D} = 3.9 A; T_{j} = 25 °C | - | 6.2 | - | S |
| R _G | gate resistance | f = 1 MHz | - | 11.8 | - | Ω |
| Dynamic ch | naracteristics | | | | | |
| Q _{G(tot)} | total gate charge | V _{DS} = 15 V; I _D = 3.9 A; V _{GS} = 10 V; | - | 3.5 | 5 | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C | - | 0.4 | - | nC |
| Q _{GD} | gate-drain charge | | - | 0.8 | - | nC |
| C _{iss} | input capacitance | V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V; | - | 157 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 34 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 27 | - | pF |
| t _{d(on)} | turn-on delay time | V _{DS} = 15 V; I _D = 3.9 A; V _{GS} = 10 V; | - | 3 | - | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$ | - | 19 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 15 | - | ns |
| t _f | fall time | | - | 8 | - | ns |
| Source-dra | in diode | | ' | • | | |
| V_{SD} | source-drain voltage | I _S = 1.9 A; V _{GS} = 0 V; T _i = 25 °C | - | 0.8 | 1.2 | V |

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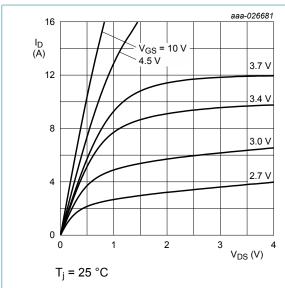


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

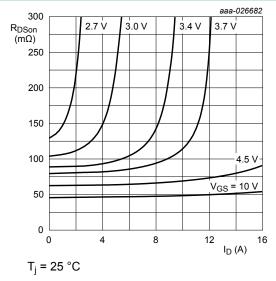


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

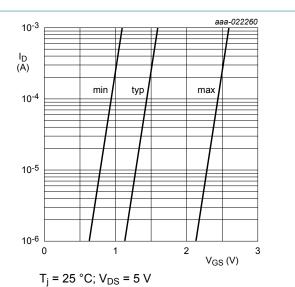


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

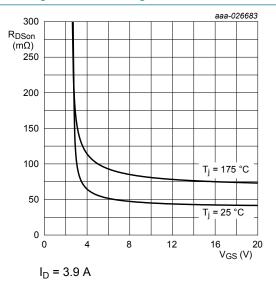


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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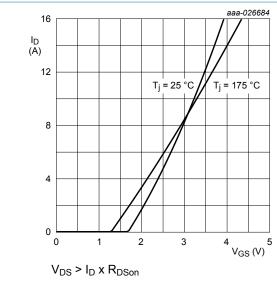


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

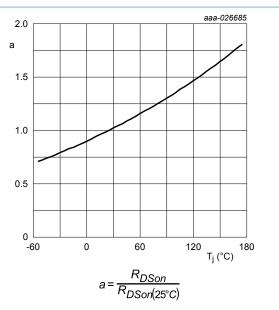


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

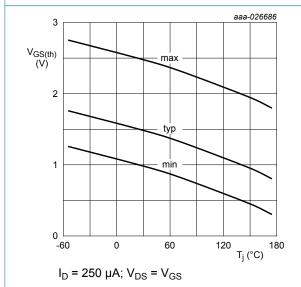


Fig. 12. Gate-source threshold voltage as a function of junction temperature

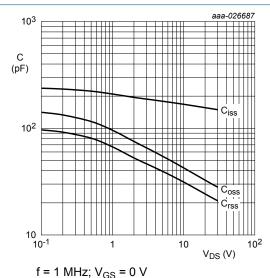
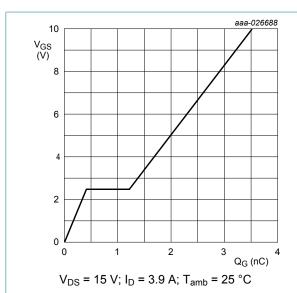


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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V_{GS}(pl)

V_{GS}(pl)

V_{GS}(th)

Q_{GS1}

Q_{GS2}

Q_{GG1}

Q_{GG2}

Q_{GG1}

Fig. 14. Gate-source voltage as a function of gate charge; typical values



Fig. 15. Gate charge waveform definitions

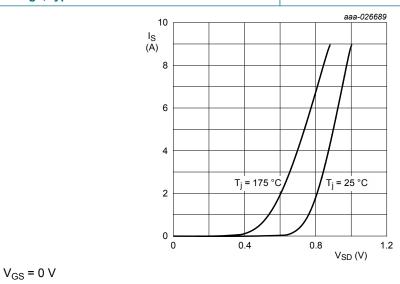
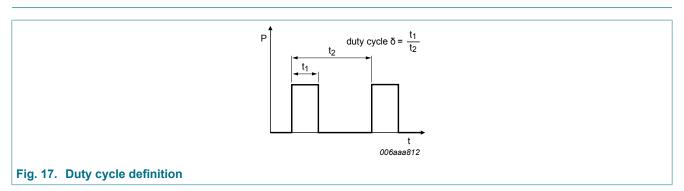


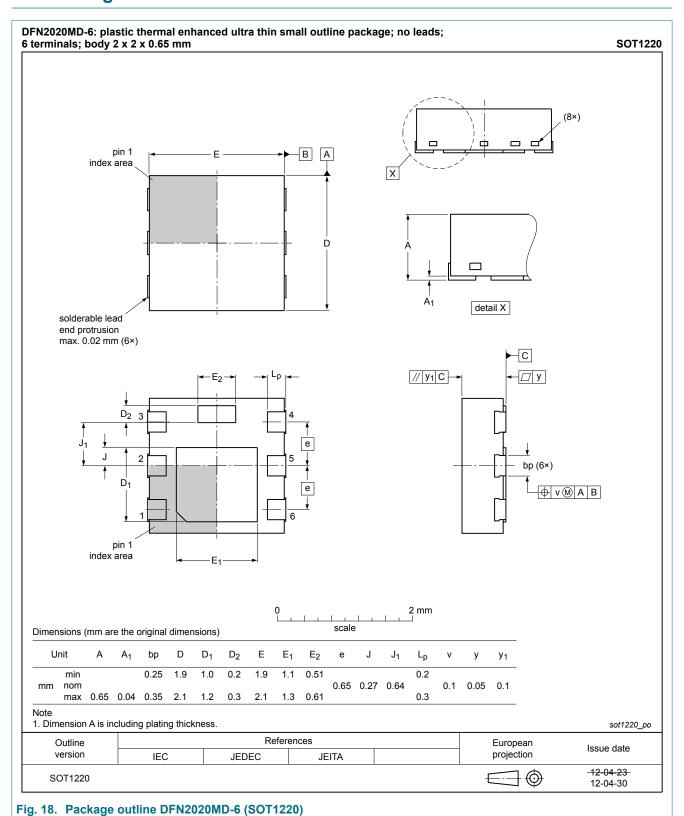
Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information



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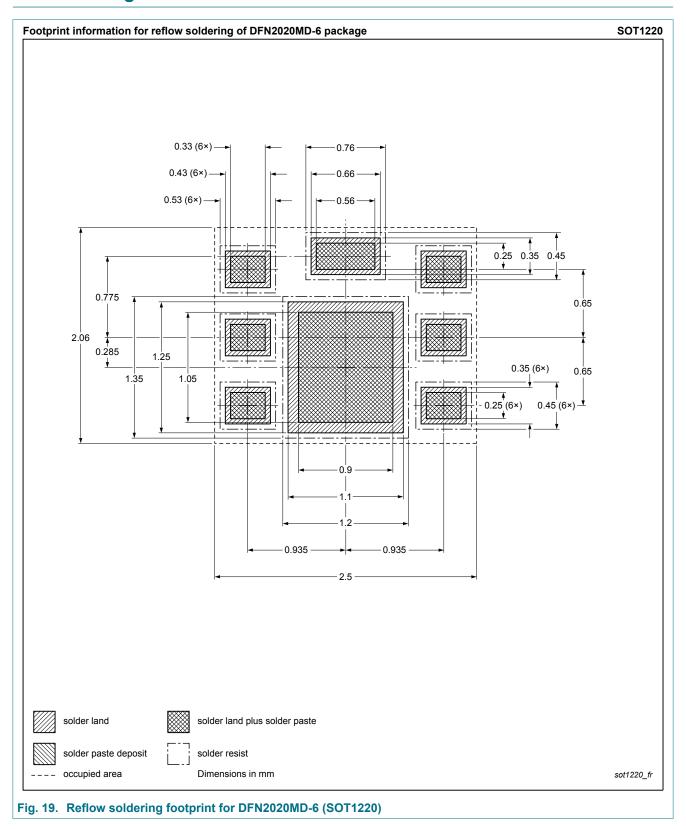
12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--------------|--------------------|---------------|------------|
| PMPB100ENE v.1 | 20180426 | Product data sheet | - | - |

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15. Legal information

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
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